ICDS Final Programme

as at 8 July 2011

Monday July 18th

0900 Welcome

0920 PLENARY TALK

Silicon Photovoltaics: Status, Defect Issues and the Emerging Role of Photoluminescence Imaging
Martin A Green, University of New South Wales, Sydney

1020 COFFEE

1050 Start of Parallel Sessions

Photovoltaics I	Theory
1050:Invited Talk	
Understanding defects in silicon photovoltaics by mechanical measurements	
J Murphy, University of Oxford, UK	
1130:PV1	**1130:Th1**
First-Principles Materials Design of $CuInSe_2$ and $Cu_2ZnSnSe_4$-Based High Efficiency Solar Cells	Performance of various finite-size supercell correction schemes in charged defect calculations
Y Tani, Osaka University, Japan	*H Komsa, Ecole Polytechnique Federale de Lausanne, Switzerland*
1150:PV2	**1150:Th3**
Vacancy Studies in $CuGaSe_2$ and $CuInSe_2$ Thin Films	First principles study of O defects in CdSe
E Korhonen, Aalto University, Finland	*J T-Thienprasert, Kasetsart University, Thailand*
1210:PV3	**1210:Th4**
Modeling of incorporation of oxygen into multi-crystalline silicon during crystal growth	Effect of O-vacancy defects on the Schottky barrier heights in Ni/SiO2 and Ni/HfO2 interfaces
Y Ohno, I Yonenaga, IMR, Tohoku University, Japan	*H Noh, Korea Advanced Institute of Science and Technology, Korea*

LUNCH 1230-1350

Photovoltaics 2	Defects in SiC
1350: Invited talk	**1350:SiC2**
Properties of iron in silicon solar cells: recombination activity, gettering, and detection methods	Characterization of deep level defects in sublimation-grown p-type 6H-SiC epilayer by deep level transient spectroscopy
D Macdonald, Australian National University, Australia	*MA Hashmi, The Islamia University of Bahawalpur, Pakistan*
	1410:SiC3
	An Improved I-V model of 4H-SiC MESFETs with multiple deep level traps (DLT)
	V L Narasimha Murty, Indian Institute of Technology – Bhubaneswar, India
1430:PV4	**1430:SiC4**
Donor-Acceptor Pair Luminescence in Compensated Si for Solar Cells	Identification of Atomic Scale Defects in 4H SiC MOSFETs Using Electrically Detected Magnetic Resonance
M Tajima, Institute of Space and Aeronautical Science/JAXA, Japan	*C Cochrane, Pennsylvania State University, USA*
1450:PV5	
The study of below and above band-edge imperfection states in In2S3 solar energy materials	
C-H Ho, National Taiwan University of Science and Technology, Taiwan	

Poster session 1

Tuesday 19th July

Defects in nanostructures	Defects in Germanium 1
0900: Invited talk	**0900:Invited Talk**
Defect and Crystal Phase Engineering of III-V Semiconductor Nanowires	First principles study of electronic and structural properties at the Ge/GeO2 interface
J Wong-Leung, Australian National University, Australia	*P Broqvist, École Polytechnique Fédérale de Lausanne, Switzerland*
0940:NS1	**0940:Ge1**
Impurity doping in semiconductor nanowires	Interfacial Conducting Layer at Ge1-ySny Grown on Si Substrate
N Fukata, International Center for Materials Nanoarchitectonics, Japan	*M Ryu, Kangwon National University, Korea*
1000:NS2	**1000:Ge2**
On the Focused Ion Beam Modification of Thin Si Lamellae	On the vacancy in germanium
E Holmström, University of Helsinki and Helsinki Institute of Physics, Finland	*S Kilpeläinen, Aalto University, Finland*

Coffee

Defects in Nitrides 1	Defects in Conducting Oxides 1
1050:Invited talk	**1050: Invited talk**
Evidence for dislocation atmospheres in the III-nitrides	Photoluminescence and exciton-phonon coupling in bulk ZnO
S Moram, University of Cambridge, UK	*R Reeves, University of Canterbury, New Zealand*
1130:N1	**1130:CO1**
Non-stoichiometric dislocations in GaN	Recombination activity of dislocations in wurtite ZnO introduced at elevated temperatures
B Hourahine, University of Strathclyde	*Y Ohno, Institute for Materials Research, Tohoku University, Japan*
1150:N2	**1150:CO2**
Hexagonal (wurtzite) GaN inclusions as a defect in cubic (zinc-blende) GaN	Structural defect complexes versus impurity centers - Shallow and deep binding centers for excitons in ZnO and related materials
N Zainal, Universiti Sains Malaysia, Malaysia	*M Wagner, Technische Universitat Berlin, Germany*
1210:N3	**1210:CO3**
Investigation of electron energy states in the InGaN/GaN multiple quantum wells	Cross-sectional electron microscopy of IrOx/ZnO Schottky diode interfaces
MA Hashmi, The Islamia University of Bahawalpur, Pakistan	*E Mayes, RMIT University, Melbourne, Australia*

LUNCH 1230-1350

Rare earths	Defects in Silicon 1
1350: Invited talk	**1350:Invited Talk**
Rare earth based compounds for photonic and photovoltaic applications,	Microdefects in germanium-doped Czochralski silicon
Maria Miritello, University of Catania, Italy	*Professor Deren Yang, Zhejiang University, China*
1430: RE1	**1430:Si1**
Enhancement of red emission in SrTiO3:Pr3+ by the addition of alliovalent cation -from the viewpoint of defect chemistry	Recombination at oxide precipitates in silicon
Yoshiyuki Inaguma, Gakushuin University,Japan	*J Murphy, University of Oxford, UK*
1450: RE2	**1450:Si2**
Determining the Structure of Rare-Earth Centres in GaN	Electronic Properties and Diffusivity of the Oxygen Dimer in Silicon
B. Hourahine, University of Strathclyde	*A R Peaker, University of Manchester, UK*

Poster session 2

Wednesday 20th July

Organic Semiconductors	Defects in Germanium 2
0850: Invited talk	**0900:Ge3**
Ion implantation effects on organic thin film transistors	Muonium Transitions in Ge-rich SiGe Alloys
B.Fraboni, Università di Bologna, Italy	*P Mengyan, Texas Tech University, USA*
0930:OS1	**0920:Ge4**
Origin and Characterization of Deep and Shallow Traps in Organic Molecular Semiconductors	The surface blistering kinetics and the H-platelet evolution in H-implanted germanium
S Ghosh, Jawaharlal Nehru University, India	*X Zhang, Institute of Microelectronics, Chinese Academy of Sciences, China*
0950: Invited talk	**0940:Ge5**
Electrically and Optically-Detected Electron Spin Resonance in PPV-based Organic Light Emitting Diodes	Oxygen in B_2O_3 encapsulated Czochralski-grown Ge
A Edgar, Victoria University, New Zealand	*I Yonenaga, IMR, Tohoku University, Japan*
	1000:Ge6
	Positron Annihilation and Deep Level Transient Spectroscopy Studies of Vacancy-related Defects in Ion Implanted Germanium
	J McCallum, University of Melbourne, Australia

Coffee

Defects in Conducting Oxides 2	Defects in Si 2
1050:CO4	**1045:Invited Talk**
Dislocation levels acting as radiative recombination centers in compound semiconductors	Laplace Deep Level Transient Spectroscopy of Silicon ... Embodiment and Evolution
Y Ohno, Institute for Materials Research, Tohoku University, Japan	*A R Peaker, University of Manchester, UK*
1110:CO5	
Charge states of a hydrogen defect (3326 cm-1 line) in ZnO	
E Lavrov, TU Dresden, IAP/Halbleiterphysik, Germany	
1130:CO6	**1130:Si3**
Structural and optical characterization of indium and nitrogen codoped ZnO	Contamination of silicon by iron at low temperatures
M Deicher, Universität des Saarlandes, Germany	*J Murphy, University of Oxford, UK*
1150:CO7	**1150:Si4**
Motion of Positively-Charged Muonium in ZnO	On the impact of stress in intrinsic defect formation during single crystal silicon growth
B Baker, Texas Tech University, USA	*J Vanhellemont, Ghent University, Belgium*
	1210:Si5
	The CuPL defect and the Cu_sCu_{i3} complex
	S Estreicher, Texas Tech University, USA

Thursday 21th July

Defects in Compound Semiconductors	Defects in Conducting Oxides 3
0850: Invited talk	**0900:CO9**
Atomic and Electronic Structures of Defects at Interfaces and in Two-Dimensional Semiconductors	Metastable properties of a shallow-level defect in ZnO grown by pulsed laser deposition
G Duscher, University of Tennessee (Knoxville), USA	*F D Auret, University of Pretoria, South Africa*
0930:CS1	**0920:CO10**
Intrinsic defects in GaAs and InGaAs through hybrid functional calculations	IR absorption study of the VZnH2 defect in ZnO
H Komsa, Ecole Polytechnique Federale de Lausanne, Switzerland	*E Lavrov, TU Dresden, IAP/Halbleiterphysik, Germany*
0950:CS2	**0940:CO11**
Nanoscale Potential Fluctuations in (GaMn)As/GaAs Heterostructures: From Individual Ions to Charge Clusters and Electrostatic Quantum Dots	Monitoring Intrinsic Defects in Ion Implanted ZnO Using Li as a Tracer
A Wijnheijmer, Eindhoven University of Technology, the Netherlands	*P Neuvonen, University of Oslo, Norway*
1010:CS3	**1000:CO12**
Defect and Disorder in High Energy Light Ion Irradiated Undoped GaAs and GaAs:Cr	Muonium Dynamics in Transparent Conducting Oxides
A Roy, Indian Institute of Technology Kharagpur, India	*Y Celebi, Texas Tech University, USA*

Coffee

Nitrides 2	Defects in Conducting Oxides 4
1050:N4	**1050:CO13**
Structural and local electrical properties of AlInN/AlN/GaN heterostructures	The role of intrinsic gap states and native defects at ZnO surfaces and interfaces
A Cavallini, University of Bologna, Italy	M *Allen, University of Canterbury, New Zealand*
1110:N5	**1110:CO14**
Structural defect anisotropy of PVT grown AlN (1-102) single crystals	Phase Diagrams of polar Surface Reconstructions of Zinc Oxide
L Kirste, Fraunhofer Institute of Applied Solid State Physics, Germany	*M Gluba, Helmholtz-Zentrum Berlin für Materialien und Energie, Germany*
1130:N6	**1130:CO15**
Defect studies in In-rich III-Nitrides with positron annihilation spectroscopy	Hydrogen shallow donor in rutile TiO2
C Rauch, Aalto University, Finland	*Herklotz F, TU Dresden, IAP/Halbleiterphysik, Germany*
1150:N7	
Local Conduction Paths in Nitride-based heterostructure	
A Minj, University of Bologna, Italy	

LUNCH 1230-1350

Defects in Si 3

1350: Invited talk

Symmetry and structure of N-O shallow donor complexes in silicon

Hans Ch. Alt, Munich University of Applied Sciences, Germany

1430:Si6

300 mm Czochralski Silicon Wafers Optimized with Respect to Voids with Laterally Homogeneous Internal Getter Capabilities

G Kissinger, IHP, Germany

Poster session 3

Friday 22nd July

Defects in Magnetic Semiconductors 1	Defects in Si 4
	0900:Si8
	Deep Level Transient Spectroscopy study of ion implantation-induced extended defects in silicon
	J Boucher, LAAS-CNRS, France
0920:Invited Talk	**0920:Si9**
Phase separation in magnetic semiconductors: Coherent aggregation of magnetic ions vs. precipitation of magnetic nanoclusters	Impact of radiation induced bulk defects on electrical properties of silicon sensors for the hl-LHC
S Kuroda, University of Tsukuba, Japan	*A Junkes, Hamburg University, Germany*
	0940:Si10
	Raman investigation of ro-vibrational modes of interstitial H_2 in Si
	E Lavrov, TU Dresden, Germany
1000:MS1	**1000:Si11**
First-Principles Study of the Magnetic Properties of Nitrogen-doped Alkaline Earth Metal Oxides	Effect of Dopants on the Photoluminescence of Interstitial-related Defect Centres in Ion Implanted Silicon
M Seike, Osaka University, Japan	*J McCallum, University of Melbourne, Australia*

Coffee

Defects in Magnetic Semiconductors 2	Defects in Si 5
1050:MS3	**1050:Si12**
Defect annealing in Mn/Fe implanted ZnO	Vacancy formation energy in Cz-Si crystals determined by a quenching method
D Naidoo, School of Physics, University of the Witwatersrand, South Africa	*I Yonenaga, Tohoku University, Japan*
1110:MS4	**1130:Si14**
Rare-earth nitrides; intrinsic ferromagnetic semiconductors	Precipitation in Silicon Wafers after High Temperature Preanneal Studied by X-ray Diffraction Methods
B Ruck, MacDiarmid Institute, Victoria University, New Zealand	*M Meduna, Masaryk University, Czech Republic*
1130:MS5	**1110:Si13**
Computational Materials Design of Filled Tetrahedral Compound Magnetic Semiconductors	Time Delayed Mössbauer Measurements on Si single-crystals
K Sato, Osaka University, Japan	*D Naidoo, University of the Witwatersrand, South Africa*

End of conference

Poster session 1 Monday afternoon

Photovoltaics

PPV.1: Evaluating Effect of Surface State Density at the Interfaces in Degraded Bulk Heterojunction Organic Solar Cell
S Arora, Zakir Husain College, University of Delhi, India

PPV.2: Photoelectrochemical Studies on Chemically Grown CdSe : Sb Thin Film Electrodes
E Masumdar, Rrajarshi Shahu Mahavidyalaya, Latur, India

PPV.3: Characterization of Al/Cu3BiS3/Buffer/ZnO Solar Cells Structure by TEM
F Mesa, Universidad Nacional de Colombia, Universidad Libre, Colombia

PPV.4: The effect of efficiency in inverted organic solar cell by thickness of ZnO electron transport layer
W Jang, School of Advanced Materials Science and Engineering, Sungkyunkwan University, Republic of Korea

PPV.5: Temperature dependence of linear thermal expansion of I-III-VI2 single crystal
A Nagaoka, University of Miyazaki, Japan

PPV.6: Optical and Electrical Characterization of ZnO Thin Films Grown by Atmospheric Spray Pyrolysis
K Naomi, Department of Electrical and Electronic Engineering, University of Miyazaki, Japan

PPV.7: Electronic structure of tin dioxide using first principles calculations
M Oshima, University of Miyazaki, Japan

PPV.8: Hybrid solar cells with p-type conducting polymer and vertically aligned n-Si nanorod: the effects of Si conductivity
S Woo, Daegu Gyeongbuk Institute of Science and Technology (DGIST), Kyungpook National University, Korea

Theory

PTh.1: First principles study of Mg-doped ZnO
N Palakawong, School of Physics, Suranaree University of Technology and Synchrotron Light Research Institute, Nakhon Ratchasima 30000, Thailand, Thailand Center of Excellence in Physics (ThEP Center), Commission on Higher Education, Bangkok 10400, Thailand

PTh.2: First-principles study of the segregation of boron dopants in Si/SiO2 interface
Y Oh, Department of Physics, Korea Advanced Institute of Science and Technology, Korea

PTh.3: Theoretical Study of Band Gap in CuAlO2: Pressure Dependence and Self-Interaction Correction
A Nakanishi, Osaka University, Japan

Silicon Carbide

PSiC.1: Study of deep level defects in doped and semi-insulating n-6H-SiC epilayers grown by sublimation method
M Asghar, The Islamia University of Bahawalpur, Pakistan

Nanostructures 1

PNS.1: Low-frequency Noise Behavior of Strained-Si/SiGe n-MOSFETs
C Mukherjee, Department of Electronics & Electrical Communicaiont Engineering, Indian Institute of Technology, Kharagpur, India

PNS.2: Defect-effects on the photoluminescence of ZrO2 bulk, film and nanocrystals
S Mochizuki, Nihon University, Japan

PNS.3: Fabrication and electrical properties of P doped ZnO nanorods by magnetron sputtering
Y Kim, School of Advanced Materials Science & Engineering, Sungkyunkwan University, Korea

PNS.4: Nanoscale Order in ZnS:(O,Cd)
S Díaz, ESIME-IPN Culhucan, Av. Sta. Ana 1000, Mexico

PNS.5: Decomposition and Unstable States of ZnTeS and CdZnTeS Alloys
S Díaz, ESIME-IPN Culhucan, Av. Sta. Ana 1000, Mexico

Diamond

PD.1: Giant concentration of nitrogen-vacancy defects in sintered detonation nanodiamonds
A Soltamova, Ioffe Physical-Technical Institute, Russia

PD.2: Optical Properties of the Neutral Silicon Split-Vacancy Centre in Diamond
B Green, University of Warwick, United Kingdom

PD.3: Uniaxial Stress Splitting Studies of the 490.8 nm and 648 nm Systems in Diamond
B Green, University of Warwick, United Kingdom

PD.4: Irradiated diamond spectra (GR-1 band)
K Boris, 1 St.-Petersburg State Medical University, Russia

PD.5: Mössbauer measurements on ion-implanted Sb/Sn in diamond
K Bharuth-Ram, University of KwaZulu-Natal, South Africia

Poster session 2 Tuesday afternoon

Rare Earths

PRE.1: Schottky barriers based on metal nanoparticles deposited onto high-purity InP layers prepared from rare-earth treated liquid phase
J Grym, Institute of Photonics and Electronics, Academy of Sciences, Czech Republic

PRE.2: Effect of Co-doping Content on Hydrothermal Derived ZnO Array Films
X He, South China University of Technology, China

Germanium

PGe.1: Stability of Valence Alternation Pairs across the Substoichiometric Region at Ge/GeO2 Interfaces
J Binder, École polytechnique fédérale de Lausanne (EPFL), Switzerland

PGe.2: On the Concentration Dependence of N-type Dopant Diffusion and Activation in Si and Ge
J Vanhellemont, Dept. of Solid State Sciences, Ghent University, Belgium

PGe.3: Characterization of electrically active defects introduced in n-Ge by hydrogen passivation
C Nyamhere, Department of Physics, Nelson Mandela Metropolitan University, PO Box 77000, Port Elizabeth 6031, South Africa

PGe.4: Doping effects for dislocation motion in Ge
Y Murao, Institute for Materials Research, Tohoku University, Japan

Nitrides

PN.1: Microstructure of Nonpolar GaN Grown at Low-temperature
Y Tokumoto, Institute for Materials Research, Tohoku University, Japan

PN.2: Surface roughness scattering limited 2DEG mobility in InAlN/AlN/GaN heterostructures
S Pandey, University of Bologna, Italy

PN.3: Electronic and magnetic properties of GaInN solid solution with manganese and hydrogen impurities
S Syrotyuk, National University Lviv Polytechnic, Ukraine

PN.4: Charge Carrier Scattering on the Short-range Potential of the Crystal Defects in Gallium Nitride
O Malyk, Lviv Polytechnic National University, Semiconductor Electronics Department

PN.5: EPR investigations of donor centers in AlN
A Soltamova, Ioffe Physical-Technical Institute, Russia

PN.6: Hydrogen Interaction with GaN Metal-Insulator-Semiconductor Diodes
Y Irokawa, National Institute for Materials Science, Japan

PN.7: Characterisation of Defects in p-GaN by Admittance Spectroscopy
K Vernon-Parry, MERI, Sheffield Hallam University, United Kingdom

Nanostructures 2

PNS.8: Structural characterizations of sol-gel synthesized TiO2 and Ce/TiO2 nanostructures
A Niltharach, Kasetsart University, Thailand

PNS.9: Novel 8x8 Field-Emission Transistor Arrays Based Single-Walled Carbon Nanotubes for Selectively Detection
K Kim, Korea Institute of Science and Technology, Korea

PNS.10: UV-laser-light-cotrolled photoluminescence of metal oxide nanostructures in different atmospheres
S Mochizuki, Nihon University, Japan

PNS.11: Theoretical study of single-walled carbon nanotubes functionalized with MEH-PPV residues: A DFT calculation
P Prajongtat, Department of Chemistry, Faculty of Science, Kasetsart University, Center of Nanotechnology KU, and NANOTEC Center of Excellence at Kasetsart University, Kasetsart University, Jatuchak, Bangkok, Thailand

PNS.12: Properties of InAs/AlAs heterostructures
V Marushak, St.-Petersburg State Medical University, 6/8 Leo Tolstoy st., St.-Petersbug 197022, Russia

PNS.13: Test challenges in analog Nano-CMOS technology
M Karmani, Electronics & Microelectronics Laboratory, Monastir, Tunisia

Organic semiconductors

POS.1: Dipole-Charge Carrier Interaction as a Source of Artificial Traps in Organic Field Effect Transistors (OFETs)
B Paez-Sierra, Thin films group, Physics department, Pontificia Universidad Javeriana, Colombia

Conducting Oxides

PCO.1: Gate bias and illumination stability of Al-doped ZnO thin-film-transistors
C Ahn, School of Advanced Materials Science and Engineering, Sungkyunkwan University, Korea

PCO.2: Influence of Annealing on UV photodetection property of Indium Zinc Oxide film
K Kim, Green Energy Research Division, Daegu-Gyeongbuk Institute of Science and Technology (DGIST), Korea

PCO.3: Investigation of Si doping effect into b-Ga2O3 film by co-sputtering of gallium oxide and Si
K Takakura, Kumamoto National College of Technology, Japan

PCO.4: Properties and identification of bound excitons in ZnO
K Johnston, CERN, CH-1211 Geneva 23, Switzerland, University of Saarlandes, 66123 Saarbrücken, Germany

PCO.5: The local environment of indium in In2O3(ZnO)m and indium doped ZnO studied with perturbed angular correlation
P Kessler, Helmholtz - Institut für Strahlen- und Kernphysik, 53115 Bonn, Germany

PCO.5 Device quality ZnO grown using a Filtered Cathodic Vacuum Arc
S Elzwawi

Poster session 3 Thursday afternoon

Silicon

PSi.1: Effect of impurities on the thermal stability of tensile strain in solid phase epitaxial regrowth formed Si:C alloy
W Woon, National Central University, Taiwan

PSi.2: Electronic properties of dislocations introduced mechanically at room temperature on single crystal silicon surface
M Ogawa, Nagoya Institute of Technology, Japan

PSi.3: Thermal evolution of surface blistering and exfoliation due to ion-implanted hydrogen monomers into Si<111>
J Liang, National Tsing Hua University, Taiwan

Psi.4: Dissolution of dislocation cores by chemical etching – application to multicrystalline silicon
J D Murpy, Department of Materials, University of Oxford, UK

PSi.5: Interaction of dopant atoms with stacking faults in Si
Y Ohno, Institute for Materials Research, Tohoku University, Japan

PSi.6: Grown-in defects in CZ-Si heavily doped with B atoms
Y Ohno, Institute for Materials Research, Tohoku University, Japan

PSi.7: Dislocation luminescence in electron beam treated silicon
L Xiang, State Key Laboratory of Silicon Materials and Department of Materials Science and Engineering, Zhejiang University, Peopleį¯s Republic of China

PSi.8: Study of Irradiation Induced Changes of Electrical and Functional Characteristics in Ge Doped Si Diodes
J Vanhellemont, Dept. of Solid State Sciences, Ghent University, Belgium

PSi.9: Three C Pairs in Si and their Interactions with H
S Estreicher, Texas Tech University, United States

PSi.10: Computational Approaches for Evaluation of Atomic Displacement Damage Using Monte Carlo Method
H Daneshvar, Shahid Beheshti University, Iran

PSi.11: Defects Engineering for Silicon Power Diode by X-ray Irradiation
P Rujanapich, Faculty of Engineering, King Mongkut's Institute of Technology Ladkrabang, Thailand

PSi.12: Non-uniform Defects Assessment by I-V and C-V characteristics of p-n junction
W Pengchan, King Mongkut's Institute of Technology Ladkrabang, Thailand

PSi.13: NBTI Degradation Effect in Thin and Thick Effective Oxide Thickness (EOT) p-MOSFET Devices
H Hussin, Faculty of Electrical Engineering, Universiti Teknologi MARA, Malaysia

PSi.14: Reconfigurations and Diffusion of Small Vacancy Clusters in Silicon
A R Peaker, University of Manchester, Manchester, United Kingdom

PSi.15: Phonon assisted photoluminescence properties of Si nanocrystals from 50 keV Ar ion induced rippled Si (100)
T Kumar, Inter-University Accelerator Centre, Aruna Asaf Ali Marg, New Delhi-110067, India

PSi.16: Diode Characteristics and Thermal Donor Formation in Germanium-doped Silicon Substrates
J Vanhellemont, Dept. of Solid State Sciences, Ghent University, Belgium

Compound Semiconductors

PCS.1: Defect detection by cathodoluminescence in semiconductor layers with built-in electric field
M Pluska, Institute of Electron Technology, Japan

PCS.2: Transients Electron Trapping Phenomenon in P-N Junction Diode Fabricated in High Energy Boron Implanted.
I Srithanachai, King Mongkut's Institute of Technology Ladkrabang, Thailand

PCS.3: Characterization of CuInGaSe2 films on Mo substrate by RF sputtering
K Yoshino, University of Miyazaki, Japan

PCS.4: On the Validity of Diffusional Model in Determination Electric Transport Parameters on Compound Semiconductors
F Mesa, Departamento de Ciencias Basicas, Universidad Libre, Bogota-Colombia, Departamento de Fisica, Universidad Nacional de Colombia, Bogota-Colombia, Colombia

PCS.5: Characterization of AgInS2 Thin Films Prepared by Vacuum Evaporation
Y Akaki, Miyakonojo National College of Technology, Japan

PCS.6: Epitaxial growth on porous III-V semiconductors
J Grym, Institute of Photonics and Electronics, Academy of Sciences, Czech Republic

PCS.7: Excitonic insulator phase in indium antimonide doped with manganese
S Obukhov, A.F.Ioffe Institute of Physics & Technology, Russia

PCS.8: Optical Characterization of GaTe layered crystal Grown by Bridgman Method
M Yoneta, Okayama University of Science, Japan

PCS9: X-ray Radiation Damage in P-N Junction Diode
I Srithanachai, King Monkut's Institute of Technology Ladkrabang, Thailand

PCS.10 Characterization of $Cu_2ZnSn(S, Se)_4$ Single Crystal by Traveling Heater Method
A. Nagaoka, University of Miyazaki, Japan

Magnetic Semiconductors

PMS.1: Room temperature GdN thin films: Resistivity and magnetization
N Plank, School of Chemical and Physical Sciences, Victoria University of Wellington, New Zealand

PMS.2: The interstitial codoping method for increasing the solubility of magnetic impurities in DMS
H Fujii, Graduate School of Engineering Science, Osaka University, Japan

PMS.3: Study of ferromagnetism in cobalt-doped ZnO diluted magnetic semiconductor
D Seghier, Science Institute, University of Iceland